

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3247	flash and peripheral and code and substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/06 16:04
L2	502	L1 and insulating	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/06 16:05
L3	33	pattern\$4 near4 (second near polysilicon) near4 insulating same (control adj gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/06 16:46
L5	208215	(ONO or (oxide near4 nitride) or O-N-O)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/06 16:47
L6	20794	(float\$4 near gate) same (control\$4 near gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/06 16:47
L7	107207	(flash near memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/06 16:47
L8	3910	L5 same L6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/06 16:47
L9	2530	L8 and L7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/06 16:47
L10	2333	L9 and cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/06 16:47

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L11	860	L10 and peripheral	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/06 16:47
L12	406	L11 and ((@ad<"20010626") or (@rlad<"20010626"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/06 16:47
L13	4108	((438/257) or (438/197)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/06 16:47
L14	78	L12 and L13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/06 16:47
L15	529	(((ONO or (oxide adj nitride adj oxide))) near8 ((control\$6 or float\$6) near2 gate)) and (((ONO or (oxide adj nitride adj oxide))) near4 (peripher\$6 or memory))) not (((ONO or (oxide adj nitride adj oxide))) near8 ((control\$6 or float\$6) near2 gate)) and (((ONO or (oxide adj nitride adj oxide))) near4 ((gate near2 (insulat\$6 or dielectric\$6))))))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/06 17:15
L16	23762	Hynix.as.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/06 18:07
L17	2	L16 and L3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/06 18:07
L18	210	(conformal near4 nitride) and flash	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/06 18:18

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L19	493	(pattern\$6 or etch\$6) near8 (second adj polysilicon) near8 insulating	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/06 18:41
L20	315	L19 and cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/06 18:41
L21	121	L20 and peripheral	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/06 18:41
L22	105	L21 and ((@ad<"20010626") or (@rlad<"20010626"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/06 18:41
L23	26	ONONO or O-N-O-N-O or (oxide adj4 nitride adj4 oxide adj4 nitride adj4 oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/06 19:05
L24	1574	(438/197).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/06 19:46
L25	2574	(438/257).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/06 19:46